

FGW75XS120

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Discrete IGBT

Discrete IGBT (XS-series)

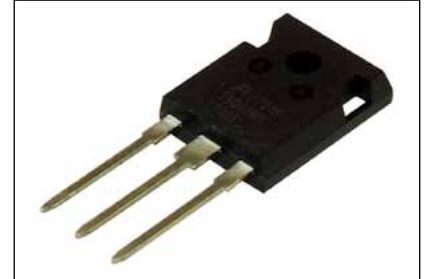
1200V / 75A

Features

Pb-free lead terminal; RoHS compliant
Halogen-free molding compound

Applications

Uninterrupted Power Supply, PV Power Conditioner,
Inverter welding machine



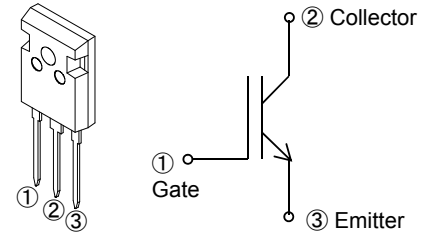
Maximum Ratings and Characteristics

● Absolute Maximum Ratings at $T_{vj} = 25^\circ\text{C}$ (unless otherwise specified)

Parameter	Symbol	Value	Unit	Remarks
Collector-Emitter Voltage	V_{CES}	1200	V	
Gate-Emitter Voltage	V_{GES}	± 20	V	
Transient Gate-Emitter Voltage		± 30	V	$t_p < 1 \mu\text{s}$
DC Collector Current	$I_{C@25}$	117	A	$T_c = 25^\circ\text{C}$
	$I_{C@100}$	75	A	$T_c = 100^\circ\text{C}$
Pulsed Collector Current	I_{CP}	300	A	Note *1
Max. Power Dissipation	P_{tot}	649	W	$T_c = 25^\circ\text{C}$
Operating Junction Temperature	T_{vj}	$-40 \sim +175$	$^\circ\text{C}$	
Storage Temperature	T_{stg}	$-55 \sim +175$	$^\circ\text{C}$	

Note *1 : Pulse width limited by $T_{vj \text{ max.}}$

Equivalent circuit



TO-247

● Electrical Characteristics at $T_{vj} = 25^\circ\text{C}$ (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE} = 1200 \text{ V}$ $V_{GE} = 0 \text{ V}$	-	-	250	μA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE} = 0 \text{ V}$ $V_{GE} = \pm 20 \text{ V}$	-	-	200	nA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 20 \text{ V}$ $I_C = 75 \text{ mA}$	4.9	5.5	6.1	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15 \text{ V}$ $I_C = 75 \text{ A}$	-	1.6	1.9	V
Input Capacitance	C_{ies}	$V_{CE} = 25 \text{ V}$ $V_{GE} = 0 \text{ V}$	-	8400	-	pF
Output Capacitance	C_{oes}	$f = 1 \text{ MHz}$	-	114	-	pF
Reverse Transfer Capacitance	C_{res}		-	68	-	pF
Gate Charge	Q_G	$V_{CC} = 600 \text{ V}$ $I_C = 75 \text{ A}$ $V_{GE} = 15 \text{ V}$	-	500	-	nC
Turn-On Delay Time	$t_{d(on)}$	$T_{vj} = 25^\circ\text{C}$	-	72	-	ns
Rise Time	t_r	$V_{CC} = 600 \text{ V}$	-	60	-	ns
Turn-Off Delay Time	$t_{d(off)}$	$I_C = 75 \text{ A}$	-	450	-	ns
Fall Time	t_f	$V_{GE} = 15 \text{ V}$	-	58	-	ns
Turn-On Energy	E_{on}	$R_G = 10 \Omega$	-	4.4	-	mJ
Turn-Off Energy	E_{off}	Energy loss include "tail" and FWD reverse recovery.	-	3	-	mJ
Turn-On Delay Time	$t_{d(on)}$	$T_{vj} = 175^\circ\text{C}$	-	78	-	ns
Rise Time	t_r	$V_{CC} = 600 \text{ V}$	-	58	-	ns
Turn-Off Delay Time	$t_{d(off)}$	$I_C = 75 \text{ A}$	-	500	-	ns
Fall Time	t_f	$V_{GE} = 15 \text{ V}$	-	108	-	ns
Turn-On Energy	E_{on}	$R_G = 10 \Omega$	-	5.6	-	mJ
Turn-Off Energy	E_{off}	Energy loss include "tail" and FWD reverse recovery.	-	4.6	-	mJ

● Thermal Resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance, Junction-Ambient	$R_{th(j-a)}$	-	-	50	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c), IGBT}$	-	-	0.231	$^\circ\text{C/W}$

Characteristics (Representative)

Figure 1. IGBT Power Dissipation vs T_c
 $T_{vj} \leq 175^\circ\text{C}$

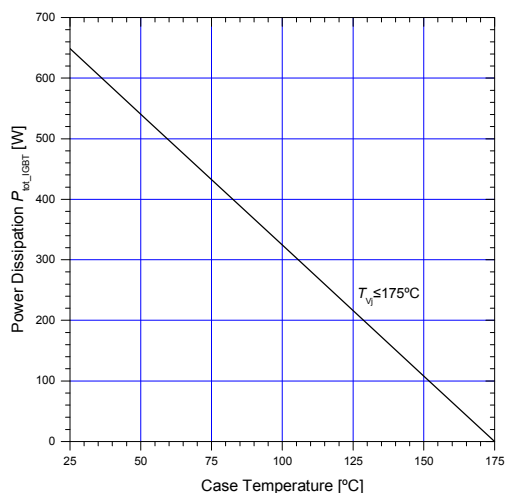


Figure 2. DC Collector Current vs T_c
 $V_{GE} \geq +15\text{ V}$, $T_{vj} \leq 175^\circ\text{C}$

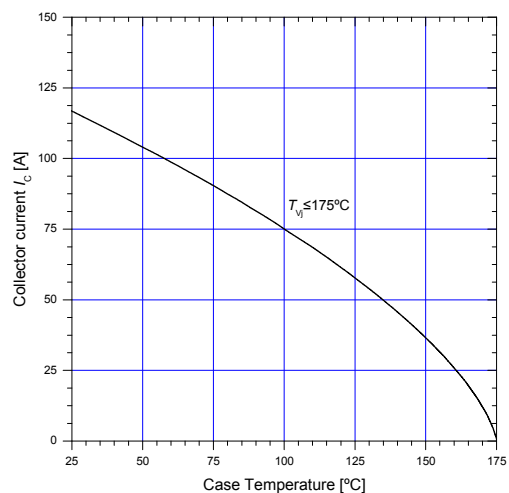


Figure 3. Typical output characteristics
 $T_{vj} = 25^\circ\text{C}$

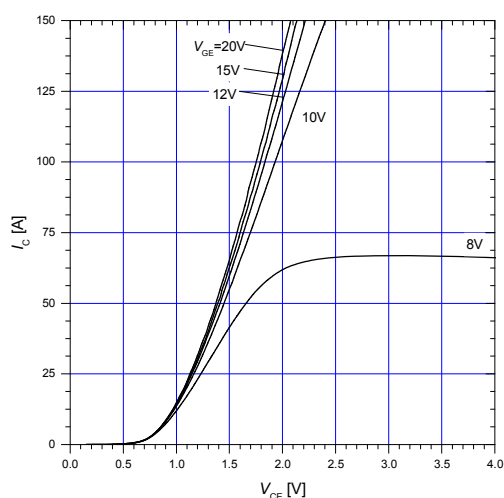


Figure 4. Typical output characteristics
 $T_{vj} = 175^\circ\text{C}$

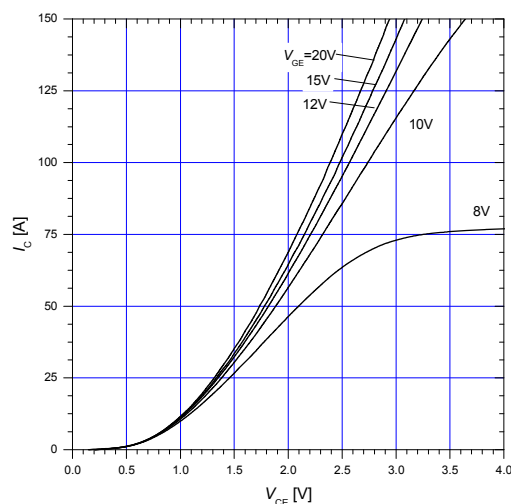


Figure 5. Typical transfer characteristics
 $V_{CE} = 20\text{ V}$

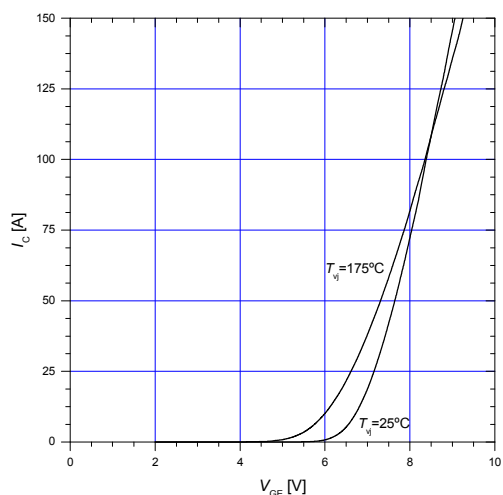


Figure 6. Gate threshold voltage
 $I_C = 75\text{ mA}$, $V_{CE} = 20\text{ V}$

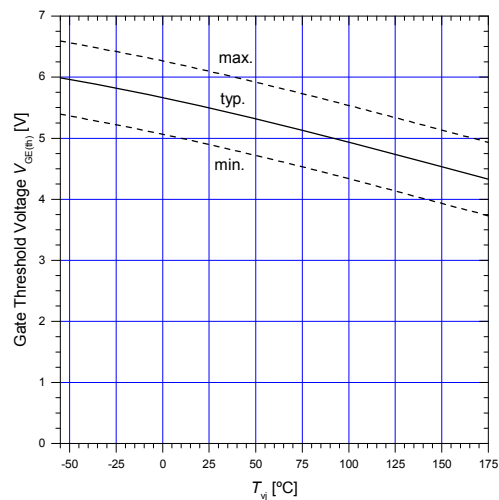


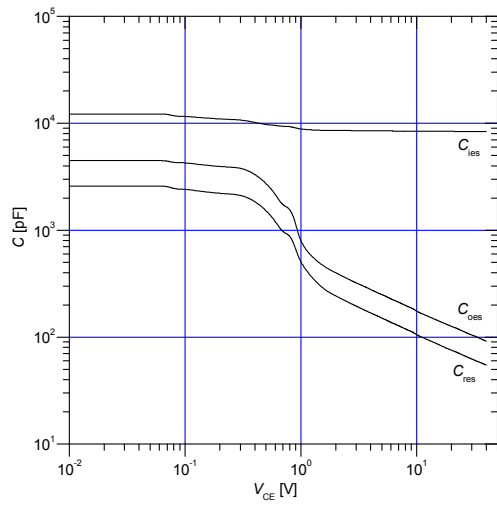
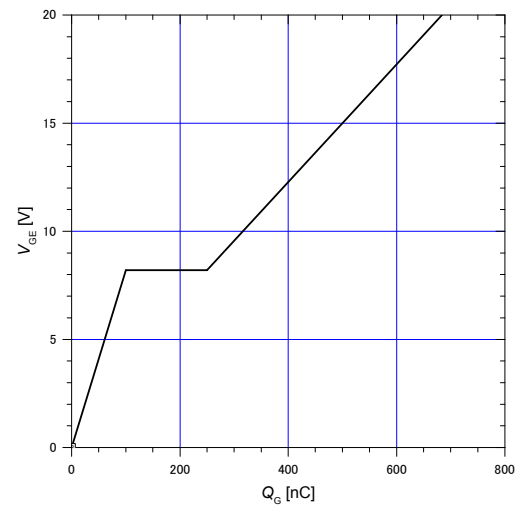
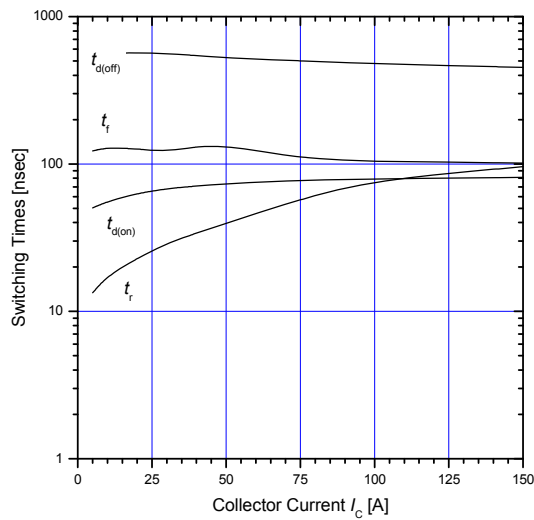
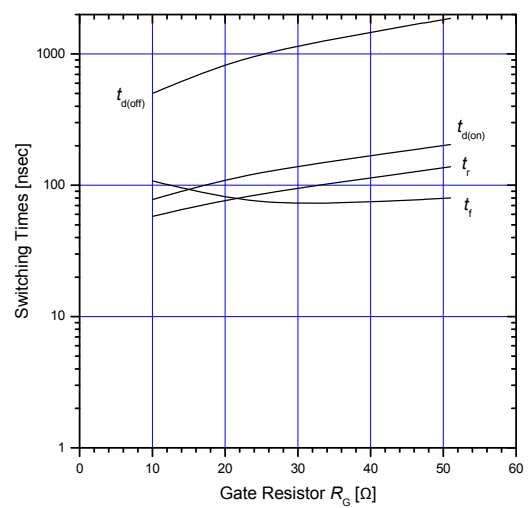
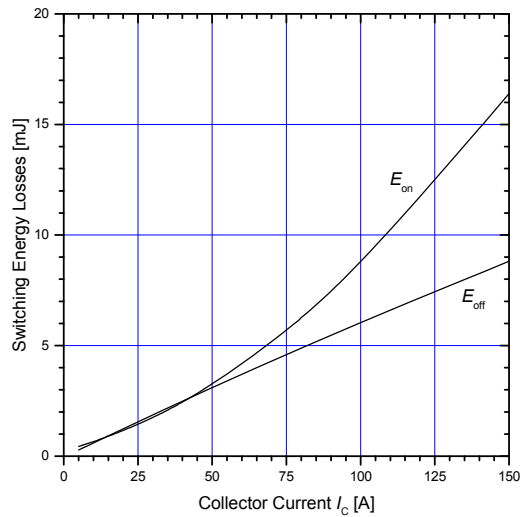
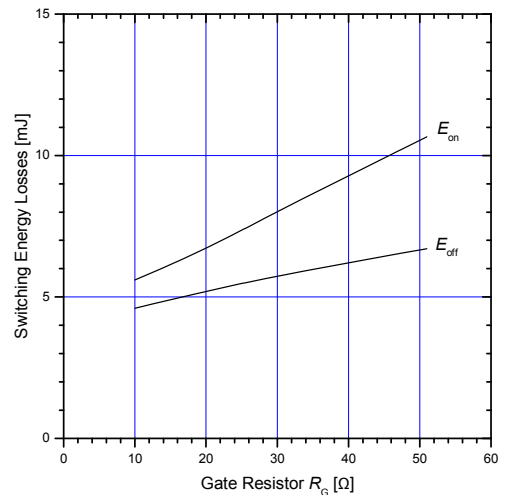
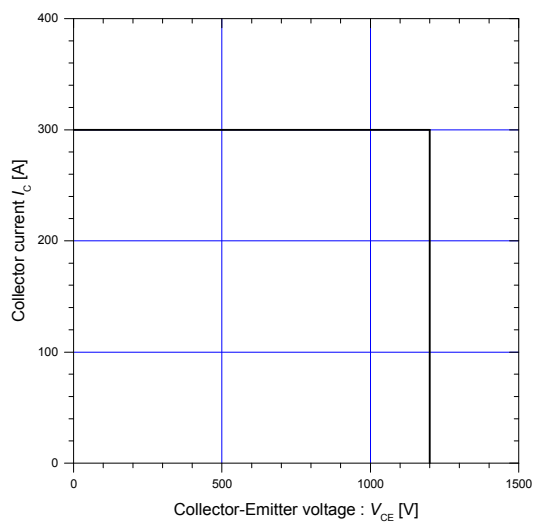
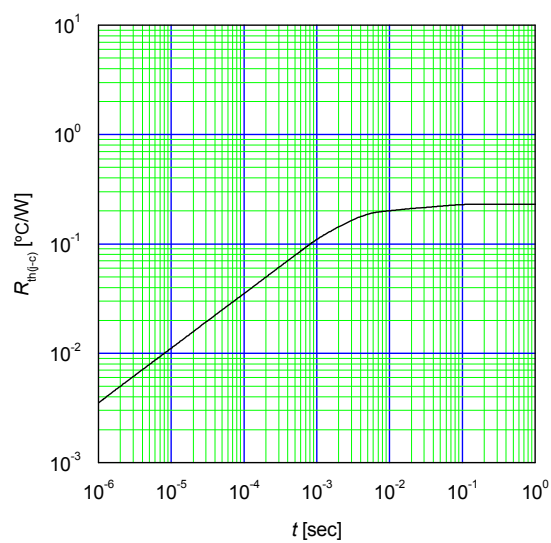
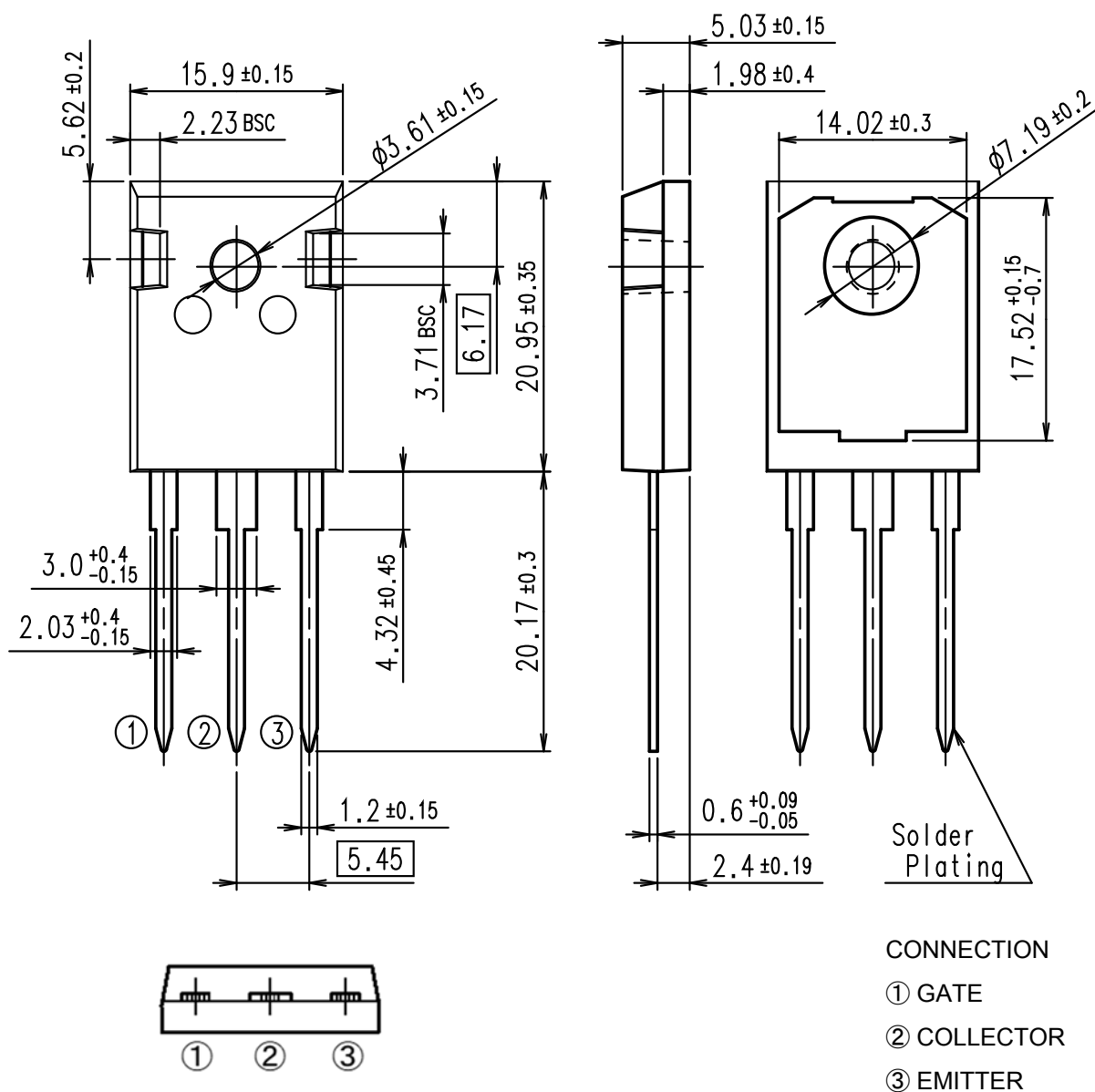
Figure 7. Typical capacitance $V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$ **Figure 8. Typical gate charge** $I_C = 75 \text{ A}, V_{CC} = 600 \text{ V}, T_{vj} = 25^\circ\text{C}$ **Figure 9. Typical switching times vs. I_C** $V_{CC} = 600 \text{ V}, V_{GE} = 15 \text{ V}, R_G = 10 \Omega, T_{vj} = 175^\circ\text{C}$ **Figure 10. Typical switching times vs. R_G** $V_{CC} = 600 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 75 \text{ A}, T_{vj} = 175^\circ\text{C}$ **Figure 11. Typical switching losses vs. I_C** $V_{CC} = 600 \text{ V}, V_{GE} = 15 \text{ V}, R_G = 10 \Omega, T_{vj} = 175^\circ\text{C}$ **Figure 12. Typical switching losses vs. R_G** $V_{CC} = 600 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 75 \text{ A}, T_{vj} = 175^\circ\text{C}$ 

Figure 13. Reverse biased safe operating area $V_{GE} = +15\text{ V} / -0\text{ V}$, $R_G = 20\ \Omega$, $T_{vj} \leq 175^\circ\text{C}$ **Figure 14. Transient Thermal Impedance of IGBT** $D = 0$ 

■ Outline Drawings, mm



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